

Picosecond Timing Workshop in Torino
16-18<sup>th</sup> of May 2018

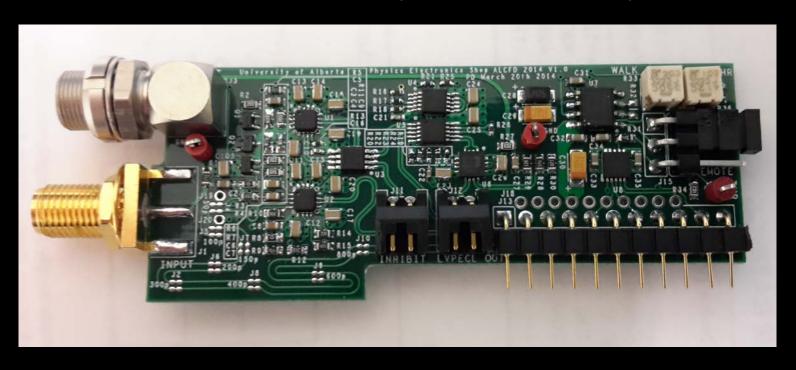
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### **AFP Constant Fraction Discriminators**

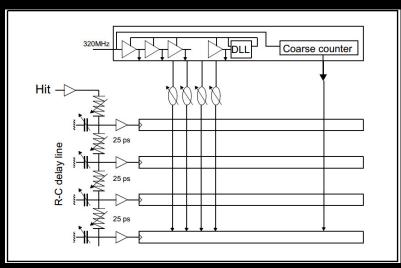
 CFDs worked well during 2017 running except for a few infant failures the cause of which still need to be investigated.
 Threshold can be set remotely. Time walk ~3ps rms



### The AFP HPTDC Board

- 12 channels with 25ps binning and ~15ps resolution
- I<sup>2</sup>C output controls CFD thresholds and trigger board settings and can read out monitoring information
- Calibration muxes allow alternate signals to be injected into the hit inputs for test and calibration purposes
- ToT implemented
- Trigger output formed from coincidence of hit signals (4ns window)





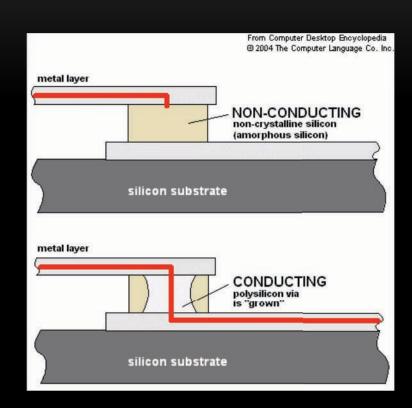
High Performance Time to Digital Converter Manual Version 2.2, March 2004, pg8. Jorgen Christiansen

# Rationale for Radiation Tolerant Upgrade of HPTDC Board

- The 32-channel HPTDC, been implemented in IBM 0.25  $\mu m$  CMOS technology
  - The HPTDC has been implemented in a radiation tolerant technology, standing up to levels of 30 Krad total dose with slight increase in power consumption.
- Current TDC FPGA chip has SEUs in configuration RAM at a much higher frequency than expected (~10 upsets/day at peak luminosity ~10<sup>34</sup> cm<sup>-2</sup> s<sup>-1</sup>).
- Originally planned mitigation, reset on SEU, would cause too much ATLAS busy. Current mitigation has potential for undetected errors.
- FPGA is being changed to a more radiation tolerant version.

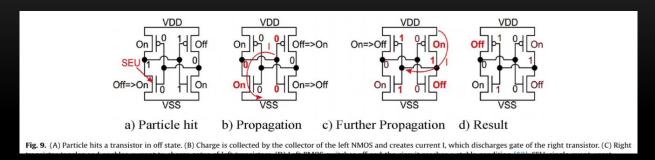
#### **Antifuse FPGAs**

- A good radiation tolerant approach to FPGA technology is the MICROSEM(ACTEL) Antifuse FPGA
- In this case the FPGA logic is one time programmable eg "hard wired" – good to few Mrads
- Problem is that each time we need to reprogram the FPGA we need a new (and expensive) FPGA.



Basic idea of an antifuse one-time Programmable FPGAs

### A Radiation Tolerant FPGA (2)



SRAM cell is formed by two inverters in a positive feedback loop. Charge injection into one of the off transistors causes a transient change of state that is then reinforced by the feedback loop

causing a bit flip. +12V Control Gate Control Gate Flating Gate

> Substrate **Program: CHE injection Erase: FN-tunneling** Write 0 Write 1

Source

**GND** 

floating

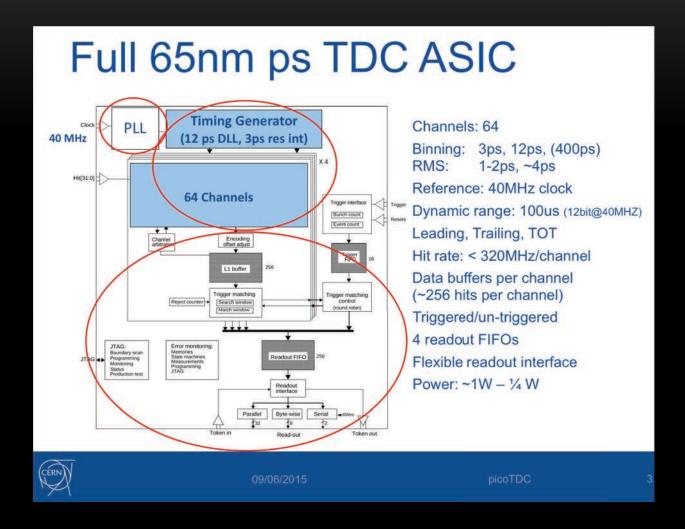
Drain

Flash memory has a floating gate. Charge is stored on the floating gate through hot carrier injection and erased via Fowler-Nordheim tunneling. No feedback Mechanism

## We Chose the Flash Technology For Installation in June 2018

- Replace existing Xilinx (SRAM ) FPGA Tech. with Microsemi Igloo2 M2GL025T (flash) FPGA.
  - Marginally smaller to the previous Xilinx FPGA 27696 vs 28848 Logic Elements
  - More RAM 1130496 bits vs 608256 & Fewer use I/O points 267 vs 238
  - Slightly slower Max Clock Rate of 400MHz vs 480MHz will result in slightly less resolution of ToT and lower granularity of trigger.
  - Igloo2 used in CMS HCAL and Muon detectors
- Some tests have been performed of the Igloo2 showing that it can take a TID of up to 100-400 Gray
- Configuration upsets practically eliminated (up to LET of 90 MeV with  $3 \times 10^9$  per cm<sup>2</sup> fluence).
- First rad. tolerant AFP HPTDCs (with flass FPGAs will be installed this June

## The Next Step - the picoTDC (1)



Jorgen Christiansen \*CERN, Moritz Horstmann, Lukas Perktold (Now AMS), Jeffrey Prinzie (KU Leuven)

## The Next Step - the picoTDC (2)

- A delivery of the current iteration of the chip is expected in June 2018. We hope to test the new chip during a late 2018 test beam
- PicoTDC uses a similar scheme for timing as current TDC but uses higher clock speed and resistive interpolation of the DLL instead of channel interpolation
- 65nm technology TID tolerant
  - SEU detection and minimize effects from SEU when it can have major consequences (system sync). As done in HPTDC.
  - Protected deploymnet needed at the HL-LHC?

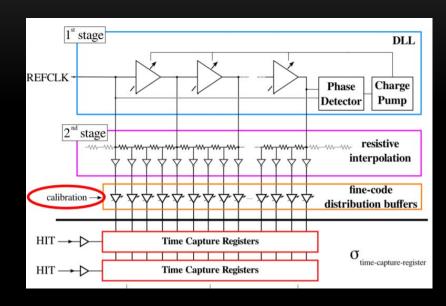


Image from picoTDC: Pico-second TDC for HEP, Jorgen Christiansen, Morit Horstmann, Lukas Perktold, Jeffery Prinzie, 2005

Max int. clock rate 2.56 GHz compared to 320 Hz for the HPTDC

# Approach to Radiation Hard Picosecond → Sub Picosecond Timing

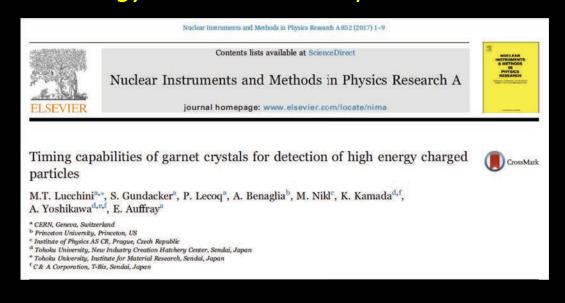
 Basic Philosophy to achieve picosecond and then sub-picosecond timing precision

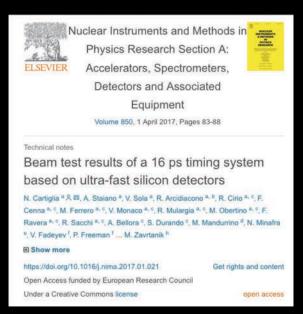


- Good per channel resolution PicoTDC 3 ps bin (1.8 ps RMS);
   HPTDC 100 ps bin.
- 2. Combine channels (eg AFP HPTDC 4 channels combined  $\rightarrow$  25ps bin width  $\rightarrow$  ~15 ps RMS)
- 3. The resolution of N uncorrelated measurements of the same quantity each with resolution  $\sigma$  has a resolution of  $\sigma/VN$  eg 30 ps measurement (detector+ readout) with 9 measurements  $\rightarrow$  10 ps resolution (30 /V 9)

# Achieving Picosecond/Sub-picosecond Timing Resolution (1)

- Picosecond/sub-picosecond timing resolution for the electronics should be possible with the picoTDC
  - When 2-4 channels are combined & RMS resolution for one channel is 1.8 ps
- The Main problem is the detector resolution. What can we assume for the best detector resolution we can get with existing/forseeable technology? It looks like 16 ps is a reasonable number.





# Achieving Picosecond/Sub-picosecond Timing Resolution (2)

- To obtain 1 ps overall resolution or better with a detector with a basic resolution of 16 ps we need at least 256 measurements!
- The detectors we mentioned can feasibly (?) make (on average)
   10 measurements per cm:
  - In the case of the crystal scintillator (eg LSO, LYSO) the thickness of the detector could be as little as ~2mm (22K photons/MeV) we have enough light to make 4 measurements/detector with 5 detectors/cm → we can make 20 measurements per cm → we would need a ~13 cm long detector.
  - We should be able to make as many measurements/cm with the Low-Gain Avalanche Detector (LGAD) design,

<b>UFSD Timing resolution</b>			
	Vbias = 200 V	Vbias = 230 V	
N = 1	34 ps	27 ps	
N = 2	24 ps	20 ps	
N = 3	20 ps	16 ps	

Dimensions	Crystal	$E_{dep}^{peak}$ $(E_{dep}^{mean})$	$\sigma_{t,corr}$
[mm <sup>3</sup> ]	type	[MeV]	[ps]
6×6×3	LYSO:Ce	2.7 (3.2)	17.5 ± 1.1
2×2×5	LSO: Ce, Ca	4.7 (5.5)	$17.2 \pm 1.0$

# Radiation Hard Solutions to Picosecond Timing?

- ATLAS is proposing UFSD as one of the technical options for the High Granularity Timing Detector<sup>1</sup> located in front of the FCAL.
- CMS is considering UFSD to be the timing detectors for the forward Precision Proton Spectrometer (CT-PPS)<sup>2</sup>.
- In both cases, the UFSD would have moderate segmentation (a few mm<sup>2</sup>) with challenging rad. requirements (several 10<sup>15</sup> neq/cm<sup>2</sup>)
- We also considered here crystal-scintillators lutetium oxyorthosilicate (LSO) & lutetium-yttrium oxyorthosilicate (LYSO). The rad. hard properties of LSO and LYSO are well established<sup>3</sup>
  - 1) D. Zerwas, ECFA 2016, High Lumi. LHC Experiments Workshop, https://indico.cern.ch/ event/524795/contributions/2237331/attachments/1349507/2036492/161006 AixLesBains.pdf
  - 2) C. Royon, N. Cartiglia, "The AFP and CT-PPS projects", Int. J. Mod. Phys. A 29, 1446017 (2014)
  - 3) R.H. Mao, L.Y. Zhang and R.-Y. Zhu, Gamma Ray Induced Radiation Damage in PWO and LSO/LYSO Crystals, Paper N32-5 in NSS 2009 Conference Record (2009).

#### **Conclusion**

1) We have achieved 15ps time resolution for the current AFP TOF system. As far as the AFP ToF electronics is concerned we appear to have a solution for LHC Run-3. Hopefully, we will have the picoTDC for Run3 making the contribution to the AFP's timing resolution negligible compared to the detector.

2) Radiation hard picosecond & (just) subpicosend detectors look feasible utilizing

PROS

existing technology at a first quick look

A number of challenging technical gotchas have to be investigated in detail, such as noise and cross-talk issues

## **EXTRA SLIDES**

### Flash Failure Mechanisms

- Hot carrier injection causes crystal defects resulting in charge being trapped in insulation between floating gate and channel eventually shielding the floating gate. ~10000+ programming cycles.
- Ionizing radiation also deposits charge in the insulating layer. Failure usually first shows as inability to erase device.
- Charge pump for generating voltages for programming/erasure can also be susceptible to radiation induced failure rendering reprogramming impossible.
- Gate propagation delay increases as floating gate becomes shielded Eventual operational errors due to timing violation. Can be mitigated with additional timing margin.